

Notice of References Cited	Application/Control No. 10/600,393	Applicant(s)/Patent Under Reexamination CHEN ET AL.	
	Examiner Toniae M. Thomas	Art Unit 2822	Page 1 of 1

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	V	Wolf, Ph.D., Stanley, Richard N. Tauber, Ph.D., "Dry Etching for VLSI Fabrication," Silicon Processing for the VLSI Era - Vol. 1 Process Technology, Lattice Press, 1986, page 536.
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.